

## CLAIMS

What is claimed is:

- 1 1. A laser alignment target comprising:
  - 2 a surface that is out of plane with and has substantially the same first
  - 3 reflectivity as an adjacent surface of the semiconductor device; and
  - 4 a sidewall having a second reflectivity different than the first reflectivity.
  
- 1 2. The laser alignment target of claim 1, wherein the surface is below the adjacent
- 2 surface.
  
- 1 3. The laser alignment target of claim 1, wherein the surface is above the adjacent
- 2 surface.
  
- 1 4. The laser alignment target of claim 1, wherein the sidewall has a height greater
- 2 than 500 Angstroms.
  
- 1 5. The laser alignment target of claim 1, wherein the sidewall forms an angle with
- 2 horizontal of greater than 60 degrees.
  
- 1 6. The laser alignment target of claim 1, wherein the surface is a substantially
- 2 orthogonal shape.

7. The laser alignment target of claim 1, wherein the surface is made of a material comprising at least one of copper, aluminum, titanium, tungsten and tantalum.

8. The laser alignment target of claim 1, wherein the sidewall reflects light of a wavelength less than 0.4 micrometers.

1 9. A semiconductor device comprising:

2 a plurality of fuses provided on a first level of interconnect; and

3 an alignment target including:

4 a surface that is out of plane with and has substantially the same first

5 reflectivity as an adjacent surface; and

6 a sidewall having a reflectivity different than the first reflectivity.

1 10. The laser alignment target of claim 9, wherein the surface is below the adjacent

2 surface.

1 11. The laser alignment target of claim 9, wherein the surface is above the adjacent

2 surface.

1 12. The laser alignment target of claim 9, wherein the sidewall has a height greater

2 than 500 Angstroms.

1 13. The laser alignment target of claim 9, wherein the sidewall forms an angle with

2 horizontal of greater than 60 degrees.

1 14. The laser alignment target of claim 1, wherein the surface is a substantially

2 orthogonal shape.

16. A method of creating a laser alignment target, the method comprising:
  - creating a surface having substantially the same first reflectivity as an adjacent surface; and
  - forming sidewalls between the surface and the adjacent surface having a second reflectivity different than the first reflectivity.
17. The method of claim 16, wherein the step of creating includes creating a trench and depositing a metal over the trench to create the surface below the adjacent surface.
18. The method of claim 16, wherein the trench is created in a dielectric layer.
19. The method of claim 16, wherein the dielectric layer contains a wiring layer.
20. The method of claim 16, wherein the step of creating includes covering a wiring element with a metal to create the surface above the adjacent surface.